

74CBTLVD3384

10-bit level-shifting bus switch with 5-bit output enables

Rev. 1 — 19 July 2011

Product data sheet

1. General description

The 74CBTLVD3384 is a dual 5-pole, single-throw bus switch. The device features two output enable inputs (\overline{nOE}) that each control five switch channels. The switches are disabled when the associated \overline{nOE} input is HIGH. Schmitt-trigger action at control inputs makes the circuit tolerant of slower input rise and fall times. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Supply voltage range from 3.0 V to 3.6 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-B/JESD36 (3.0 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- 5 Ω switch connection between two ports
- -3 dB bandwidth at 600 MHz
- Rail to rail switching on data I/O ports
- CMOS low power consumption
- Latch-up performance exceeds 250 mA per JESD78B Class I level A
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74CBTLVD3384DK	-40 °C to +125 °C	SSOP24 ^[1]	plastic shrink small outline package; 24 leads; body width 3.9 mm; lead pitch 0.635 mm	SOT556-1
74CBTLVD3384PW	-40 °C to +125 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1
74CBTLVD3384BQ	-40 °C to +125 °C	DHVQFN24	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 × 5.5 × 0.85 mm	SOT815-1

[1] Also known as QSOP24 package

4. Functional diagram

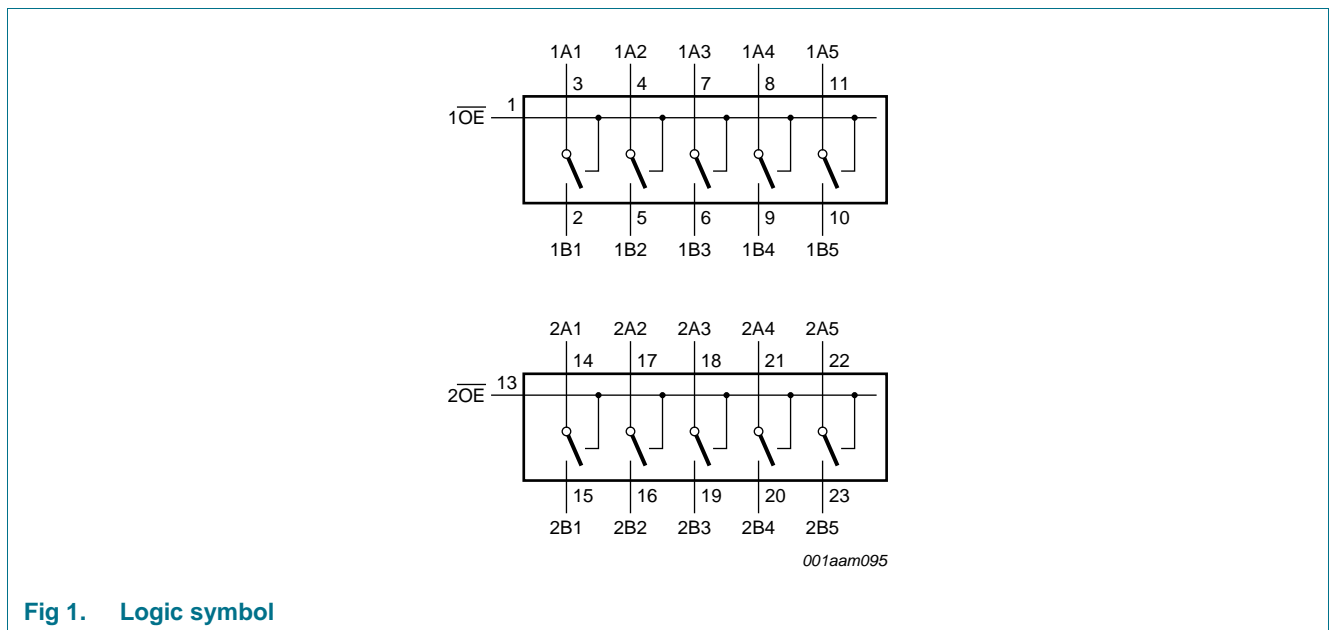


Fig 1. Logic symbol

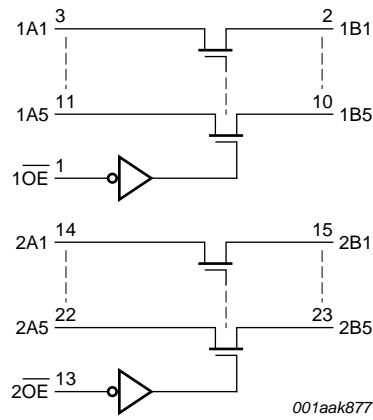


Fig 2. Logic diagram

5. Pinning information

5.1 Pinning

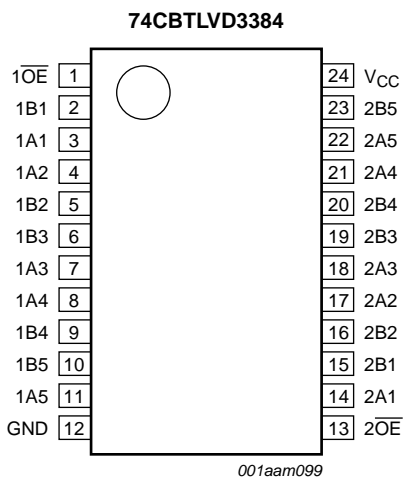


Fig 3. Pin configuration for TSSOP24 (SOT355-1)

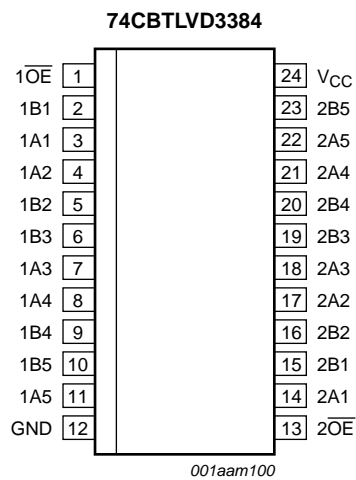
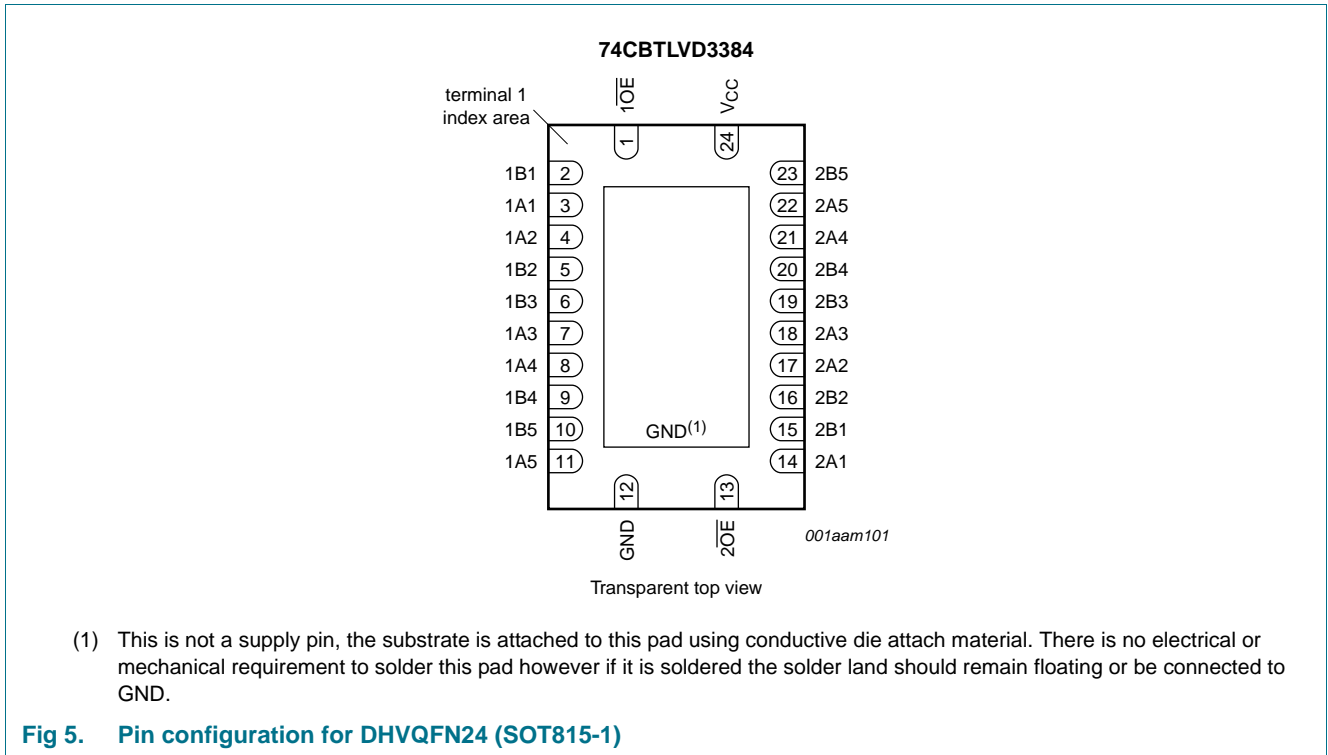


Fig 4. Pin configuration for SSOP24 (SOT556-1)



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{1OE}$, $\overline{2OE}$	1, 13	output enable input (active LOW)
1A1 to 1A5	3, 4, 7, 8, 11	data input/output (A port)
2A1 to 2A5	14, 17, 18, 21, 22	data input/output (A port)
1B1 to 1B5	2, 5, 6, 9, 10	data input/output (B port)
2B1 to 2B5	15, 16, 19, 20, 23	data input/output (B port)
GND	12	ground (0 V)
V _{CC}	24	positive supply voltage

6. Functional description

Table 3. Function selection^[1]

Input		Input/output	
$\overline{1OE}$	$\overline{2OE}$	1An, 1Bn	2An, 2Bn
L	L	1An = 1Bn	2An = 2Bn
L	H	1An = 1Bn	Z
H	L	Z	2An = 2Bn
H	H	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage		[1] -0.5	+4.6	V
V _{SW}	switch voltage	enable and disable mode	[1] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _{IO} < -0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V	-50	-	mA
I _{SW}	switch current	V _{SW} = 0 V to V _{CC}	-	±128	mA
I _{CC}	supply current		-	+100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	500	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SSOP24 and TSSOP24 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

For DHVQFN24 package: P_{tot} derates linearly at 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		3.0	3.6	V
V _I	input voltage		0	3.6	V
V _{SW}	switch voltage	enable and disable mode	0	V _{CC}	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.0 V to 3.6 V	[1] 0	200	ns/V

[1] Applies to control signal levels.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 3.0 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 3.0 V to 3.6 V	-	-	0.9	-	0.9	V
I _I	input leakage current	pin nOE; V _I = GND to V _{CC} ; V _{CC} = 3.6 V	-	-	±1	-	±20	μA
V _{pass}	pass voltage	V _I = V _{CC} ; see Figure 9 to Figure 12	-	-	-	-	-	V

Table 6. Static characteristics ...continued

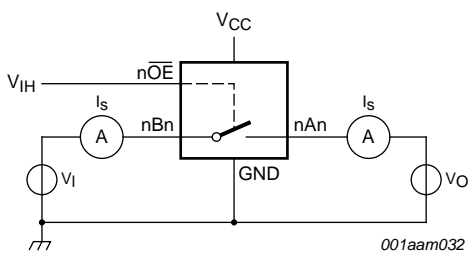
At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
I _{S(OFF)}	OFF-state leakage current	V _{CC} = 3.6 V; see Figure 6	-	-	±1	-	±20	μA
I _{S(ON)}	ON-state leakage current	V _{CC} = 3.6 V; see Figure 7	-	-	±1	-	±20	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±10	-	±50	μA
I _{CC}	supply current	V _I = V _{CC} ; I _O = 0 A; V _{CC} = 3.6 V; V _{SW} = GND or V _{CC}	-	-	20	-	50	μA
		V _I = GND; I _O = 0 A; V _{CC} = 3.6 V; V _{SW} = GND or V _{CC}	-	-	100	-	150	μA
ΔI _{CC}	additional supply current	pin n $\overline{\text{OE}}$; V _I = V _{CC} - 0.6 V; V _{SW} = GND or V _{CC} ; V _{CC} = 3.6 V	[2]	-	300	-	2000	μA
C _I	input capacitance	pin n $\overline{\text{OE}}$; V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	0.9	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance	V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	2.5	-	-	-	pF
C _{S(ON)}	ON-state capacitance	V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	9.0	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

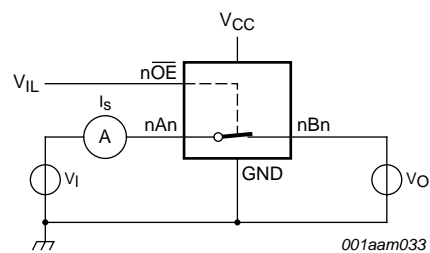
[2] One input at 3 V, other inputs at V_{CC} or GND.

9.1 Test circuits



V_I = V_{CC} or GND and V_O = GND or V_{CC}.

Fig 6. Test circuit for measuring OFF-state leakage current (one switch)



V_I = V_{CC} or GND and V_O = open circuit.

Fig 7. Test circuit for measuring ON-state leakage current (one switch)

9.2 Typical pass voltage graphs

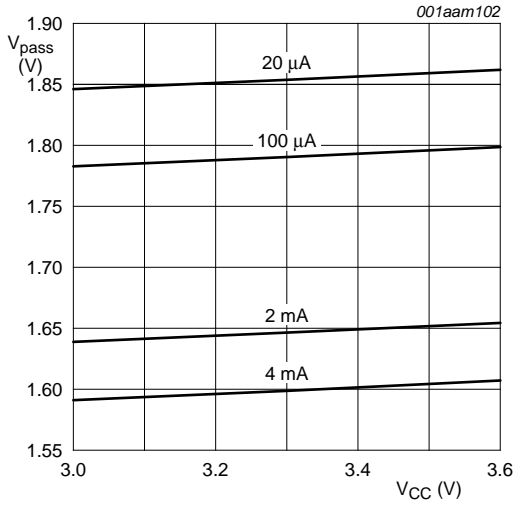


Fig 8. Pass voltage versus supply voltage; T_{amb} = 125 °C (typical)

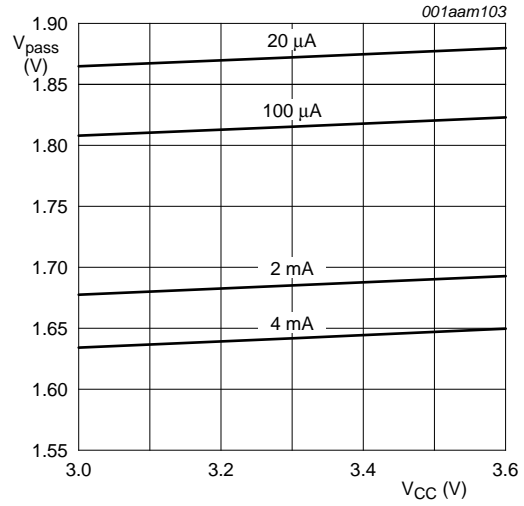


Fig 9. Pass voltage versus supply voltage; T_{amb} = 85 °C (typical)

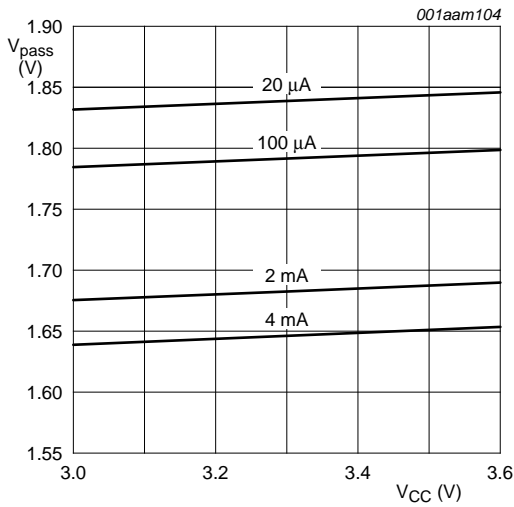


Fig 10. Pass voltage versus supply voltage; T_{amb} = 25 °C (typical)

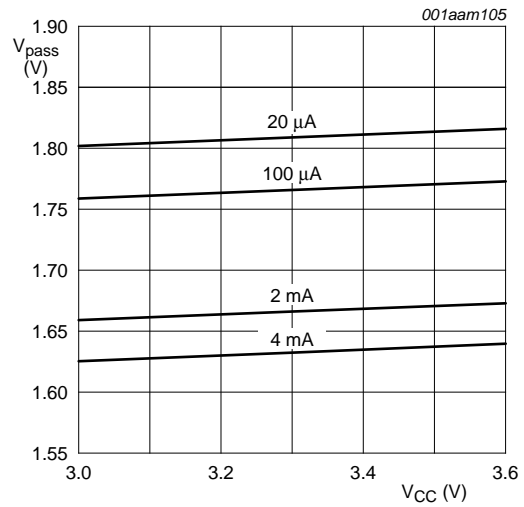


Fig 11. Pass voltage versus supply voltage; T_{amb} = 0 °C (typical)

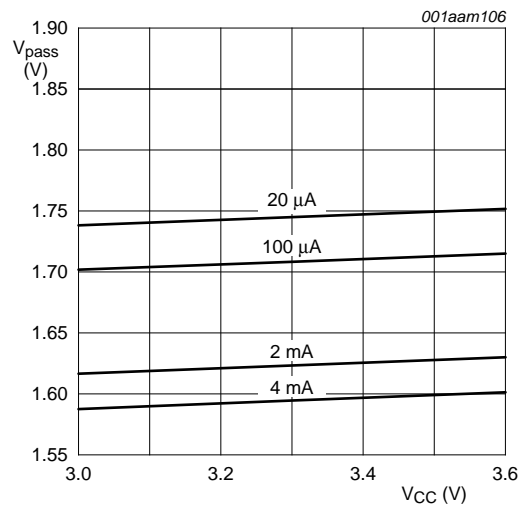


Fig 12. Pass voltage versus supply voltage; T_{amb} = -40 °C (typical)

9.3 ON resistance

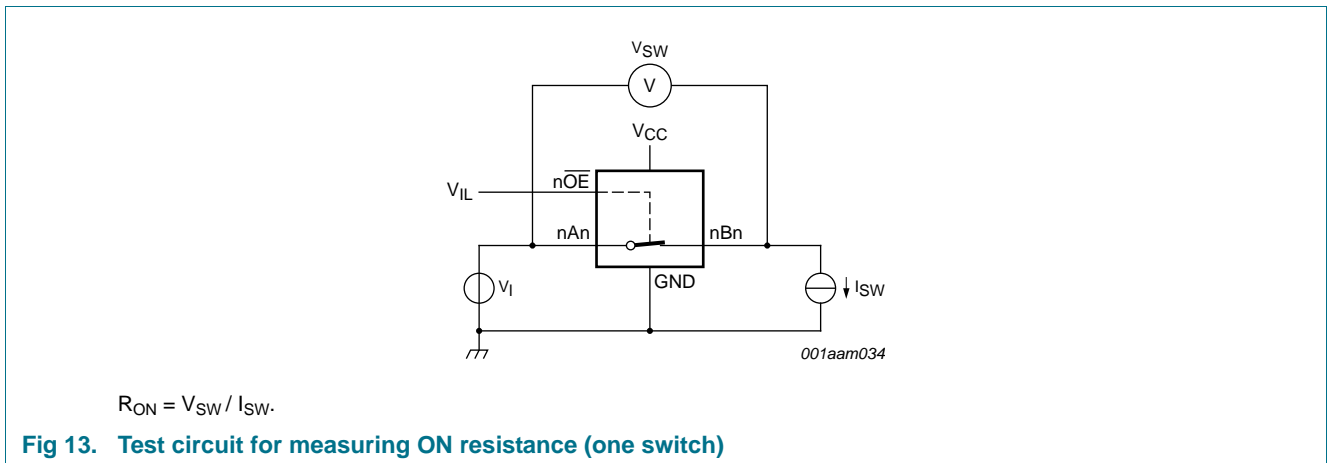
Table 7. Resistance R_{ON}

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
R _{ON}	ON resistance	V _{CC} = 3.0 V to 3.6 V ^[2]						
		I _{SW} = 64 mA; V _I = 0 V	-	3.7	7.0	-	10.0	Ω
		I _{SW} = 24 mA; V _I = 0 V	-	3.7	7.0	-	10.0	Ω
		I _{SW} = 15 mA; V _I = 1.2 V	-	4.7	10.0	-	12.0	Ω

- [1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.
- [2] Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

9.4 ON resistance test circuit



10. Dynamic characteristics

Table 8. Dynamic characteristics
GND = 0 V; for test circuit see Figure 16

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nAn to nBn or nBn to nAn; see Figure 14 V _{CC} = 3.0 V to 3.6 V	-	-	0.11	-	0.22	ns
t _{en}	enable time	nOE to nAn or nBn; see Figure 15 V _{CC} = 3.0 V to 3.6 V	1.5	2.8	5.0	1.5	6.0	ns
t _{dis}	disable time	nOE to nAn or nBn; see Figure 15 V _{CC} = 3.0 V to 3.6 V	0.8	3.2	7.0	0.8	8.0	ns

- [1] All typical values are measured at T_{amb} = 25 °C and at nominal V_{CC}.
- [2] The propagation delay is the calculated RC time constant of the on-state resistance of the switch and the load capacitance, when driven by an ideal voltage source (zero output impedance).
- [3] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [4] t_{en} is the same as t_{PZH} and t_{PZL}.
- [5] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

11. Waveforms

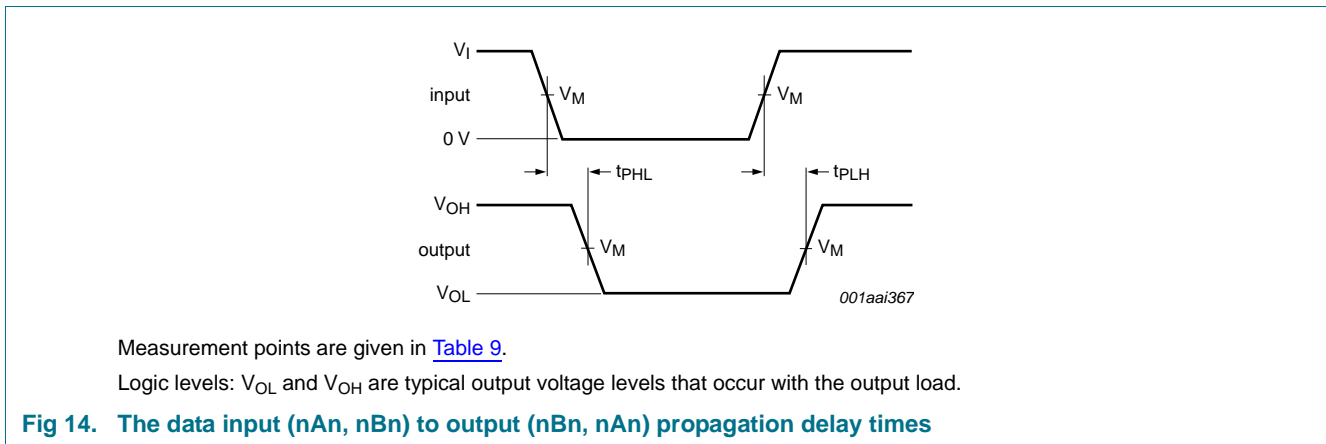
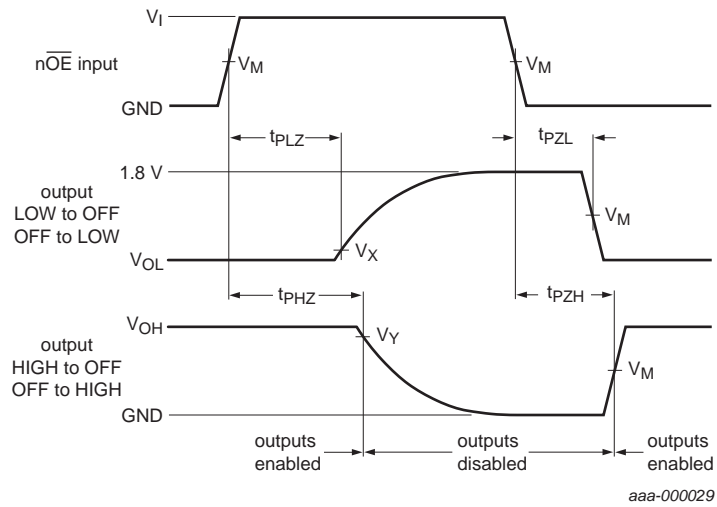


Table 9. Measurement points

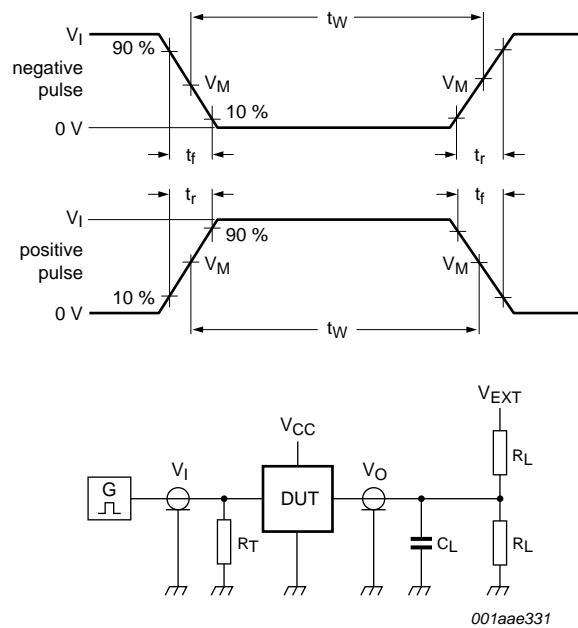
Supply voltage	Input			Output		
V _{CC}	V _M	V _I	t _r = t _f	V _M	V _X	V _Y
3.0 V to 3.6 V	0.5V _{CC}	V _{CC}	≤ 2.0 ns	0.9 V	V _{OL} + 0.15 V	V _{OH} - 0.15 V



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. Enable and disable times



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 16. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
3.0 V to 3.6 V	30 pF	1 kΩ	open	GND	3.6 V

11.1 Additional dynamic characteristics

Table 11. Additional dynamic characteristics

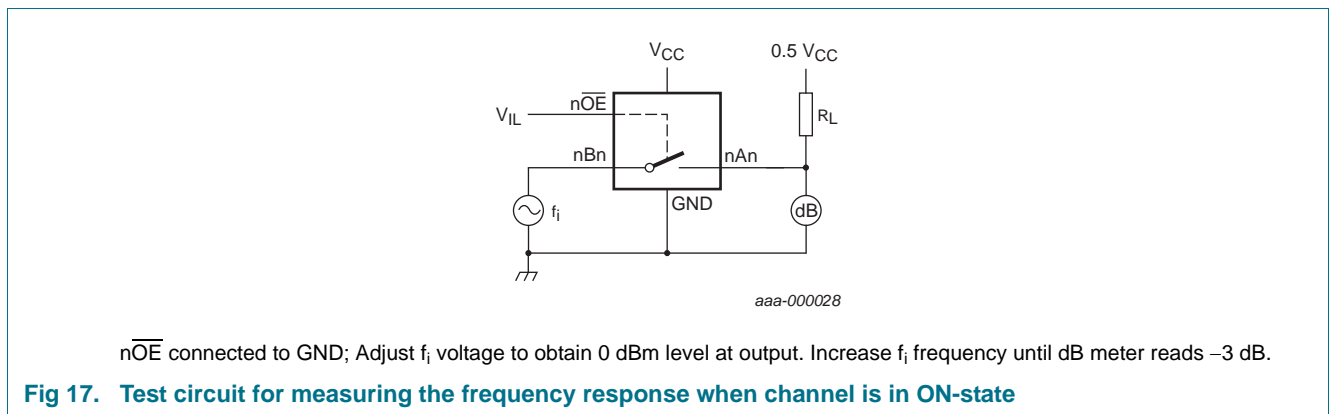
At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$.

Symbol	Parameter	Conditions	$T_{\text{amb}} = 25 \text{ }^\circ\text{C}$			Unit
			Min	Typ ^[1]	Max	
$f_{(-3\text{dB})}$	-3 dB frequency response	$V_{CC} = 3.3 \text{ V}$; $R_L = 50 \text{ } \Omega$; see Figure 17	-	575	-	MHz

[1] Typical values are measured at $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$ and $V_{CC} = 3.3 \text{ V}$.

[2] f_i is biased at $0.5V_{CC}$.

11.2 Test circuits



12. Package outline

SSOP24: plastic shrink small outline package; 24 leads; body width 3.9 mm; lead pitch 0.635 mm SOT556-1

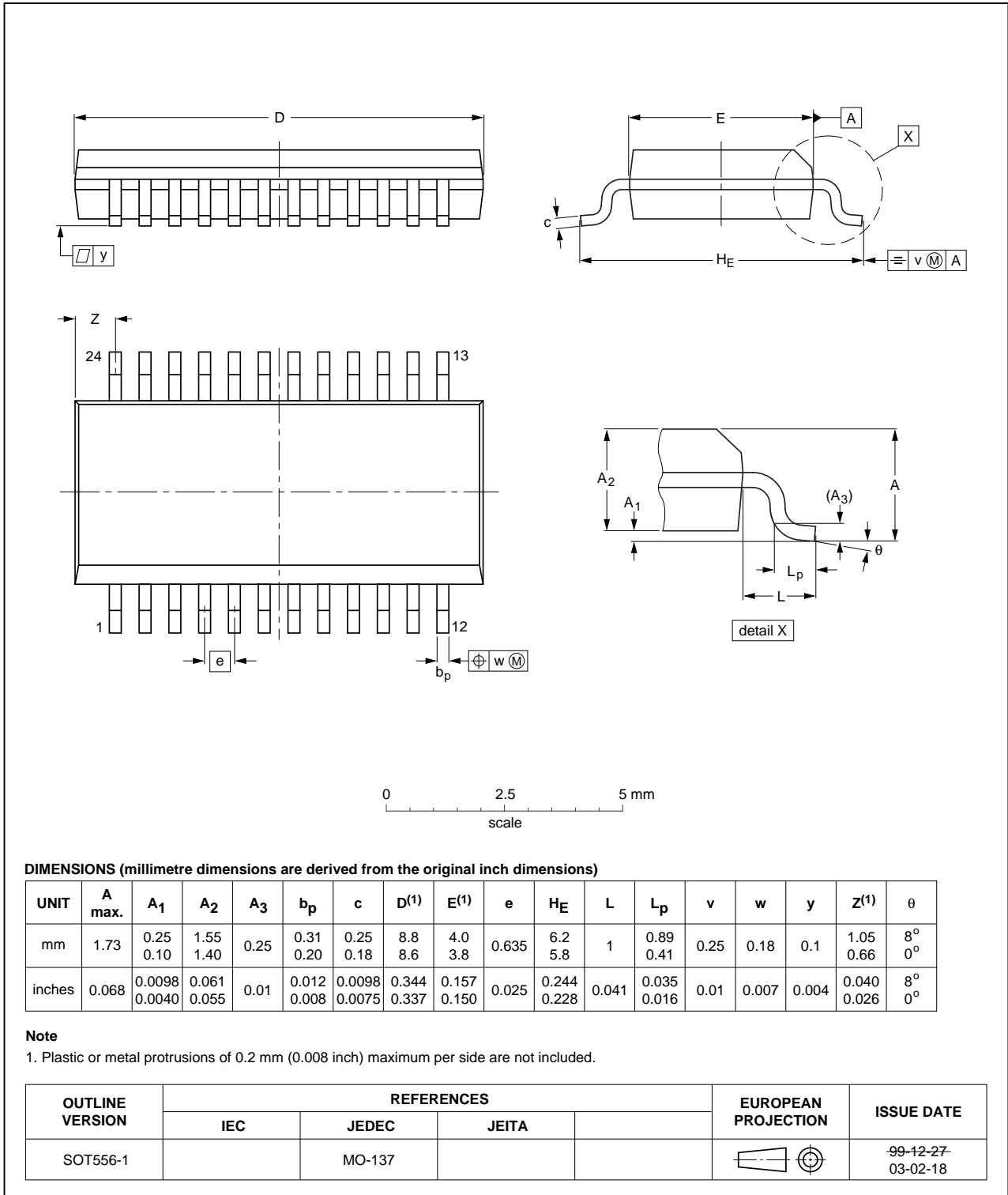


Fig 18. Package outline SOT556-1 (SSOP24)

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1

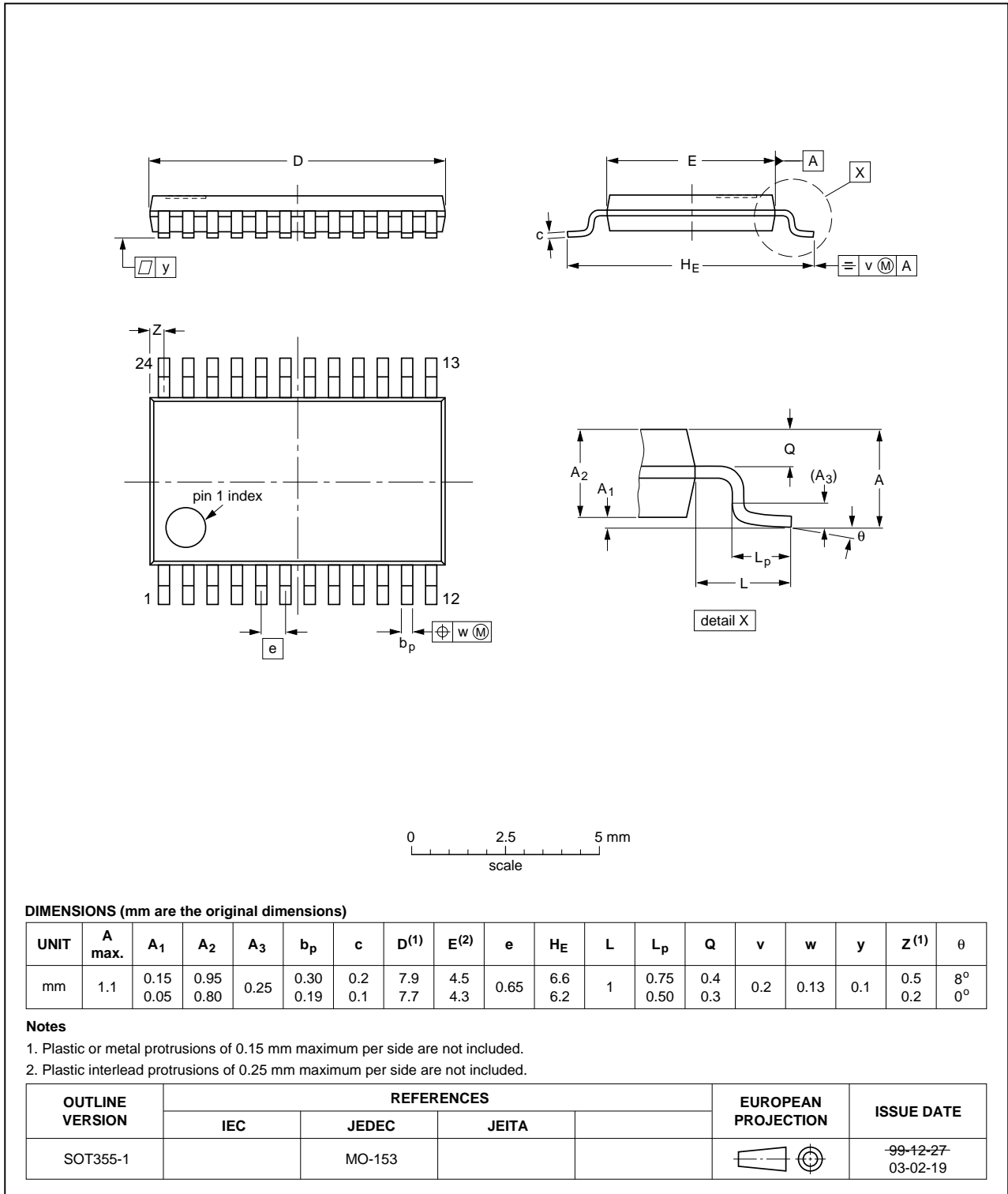


Fig 19. Package outline SOT355-1 (TSSOP24)

DHVQFN24: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 x 5.5 x 0.85 mm

SOT815-1

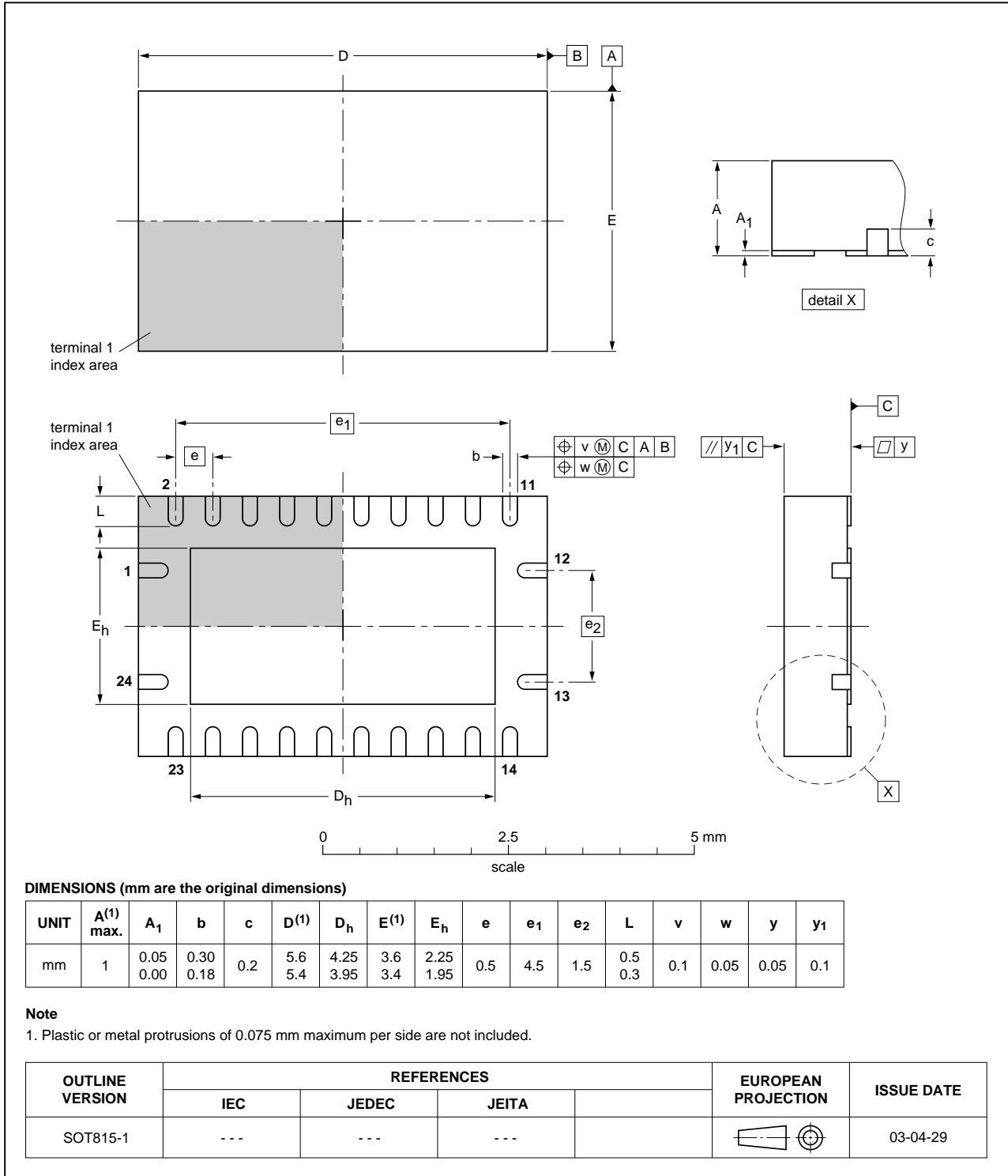


Fig 20. Package outline SOT815-1 (DHVQFN24)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74CBTLVD3384 v.1	20110719	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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